

# Woojin Choi

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/10894989/publications.pdf>

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10  
papers

1,054  
citations

1039406

9  
h-index

1372195

10  
g-index

10  
all docs

10  
docs citations

10  
times ranked

1854  
citing authors

#	ARTICLE	IF	CITATIONS
1	Strain engineering and epitaxial stabilization of halide perovskites. Nature, 2020, 577, 209-215.	13.7	417
2	A fabrication process for flexible single-crystal perovskite devices. Nature, 2020, 583, 790-795.	13.7	278
3	High-Voltage and Low-Leakage-Current Gate Recessed Normally-Off GaN MIS-HEMTs With Dual Gate Insulator Employing PEALD- $\text{SiN}_x$ /RF-Sputtered- $\text{HfO}_2$ . IEEE Electron Device Letters, 2014, 35, 175-177.	2.2	100
4	Controlled Homoepitaxial Growth of Hybrid Perovskites. Advanced Materials, 2018, 30, e1705992.	11.1	82
5	Si Complies with GaN to Overcome Thermal Mismatches for the Heteroepitaxy of Thick GaN on Si. Advanced Materials, 2017, 29, 1702557.	11.1	53
6	High-Quality ICPCVD $\text{SiO}_2$ for Normally Off AlGaIn/GaN-on-Si Recessed MOSHFETs. IEEE Electron Device Letters, 2013, 34, 354-356.	2.2	51
7	Vertical ZnO Nanotube Transistor on a Graphene Film for Flexible Inorganic Electronics. Small, 2018, 14, e1800240.	5.2	25
8	Structural and electrical characterization of thick GaN layers on Si, GaN, and engineered substrates. Journal of Applied Physics, 2019, 125, .	1.1	22
9	Intrinsically Linear Transistor for Millimeter-Wave Low Noise Amplifiers. Nano Letters, 2020, 20, 2812-2820.	4.5	16
10	A Non-GCA DG MOSFET Model Continuous into the Velocity Saturation Region. IEEE Transactions on Electron Devices, 2019, 66, 1160-1166.	1.6	10